

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







VTP Process Photodiodes

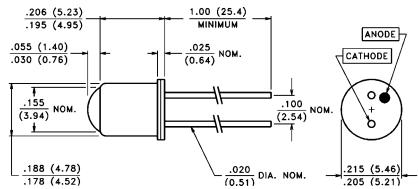
VTP1112H



PRODUCT DESCRIPTION

Small area planar silicon photodiode in a lensed. dual lead TO-46 package. Cathode is common to the case. These diodes exhibit low dark current under reverse bias and fast speed of response.

PACKAGE DIMENSIONS inch (mm)



CASE 19 TO-46 LENSED HERMETIC CHIP ACTIVE AREA: .0025 in² (1.6 mm²)

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C
Operating Temperature: -40°C to 110°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP1112H			LINITO
			Min.	Тур.	Max.	- UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	30	90		μΑ
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.20		%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		350		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, VR = 50 V			7	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		.5		GΩ
CJ	Junction Capacitance	H = 0, V = 15 V			6	pF
Re	Responsivity	940 nm		.033		A/(W/cm ²)
S _R	Sensitivity	@ Peak		.55		A/W
λ_{range}	Spectral Application Range		400		1150	nm
λ_{p}	Spectral Response - Peak			925		nm
V_{BR}	Breakdown Voltage		50	140		V
θ _{1/2}	Angular Resp 50% Resp. Pt.			±15		Degrees
NEP	Noise Equivalent Power		8.7 x 10 ⁻¹⁴ (Typ.)			W∕√Hz
D*	Specific Detectivity		1.5 x 10 ¹² (Typ.)			cm√Hz/W